

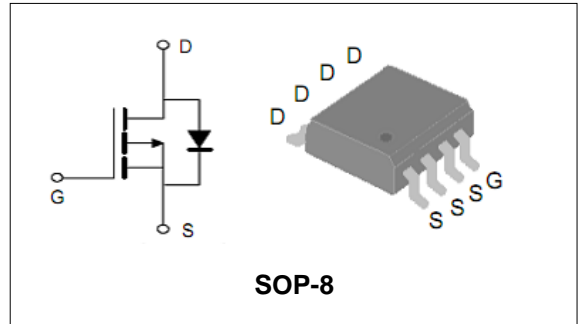
**-30V P-Channel Enhancement Mode MOSFET****Features**

- Advanced trench process technology.
- High Density Cell Design For Ultra Low On-Resistance

BVDSS	-30	V
ID	-7	A
RDSON@VGS=-4.5V	36	mΩ
RDSON@VGS=-10V	25	mΩ

Applications

- PWM applications
- Load switch
- Power management

**Order Information**

Product	Package	Marking	Reel Size	Reel	Carton
PTS30P07	SOP-8	PTS30P07	13inch	3000PCS	48000PCS

Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)			
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	-30	V
V_{GS}	Gate-Source Voltage	±20	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
I_S	Diode Continuous Forward Current	$T_A = 25^\circ\text{C}$ -7	A
Mounted on Large Heat Sink			
I_{DM}	Pulse Drain Current Tested (Silicon Limit) (Note1)	$T_A = 25^\circ\text{C}$ -28	A
I_D	Continuous Drain current	$T_A = 25^\circ\text{C}$ -7	A
P_D	Maximum Power Dissipation	$T_A = 25^\circ\text{C}$ 1.8	W
$R_{\theta JA}$	Thermal Resistance Junction-to-Ambient (Note2)	69.4	°C/W

**-30V P-Channel Enhancement Mode MOSFET**

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
V _{(BR)DSS}	Drain- Source Breakdown Voltage	VGS=0V ID=-250μA	-30	--	--	V
I _{DSS}	Zero Gate Voltage Drain current	VDS=-30V,VGS=0V	--	--	-1	μA
I _{GSS}	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
V _{GS(TH)}	Gate Threshold Voltage	VDS=VGS,ID=-250μA	-1.1	-1.5	-2.2	V
R _{DS(ON)}	Drain-Source On-State Resistance (Note3)	VGS=-10V, ID=-7A	--	25	34	mΩ
		VGS=-4.5V, ID=-4A	--	36	46	mΩ
g _{FS}	Forward Transconductance	VDS=-10V,ID=-7A	--	21	--	S
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated) (Note4)						
C _{iss}	Input Capacitance	VDS= -15V, VGS=0V, F=1MHz	--	1320	--	pF
C _{oss}	Output Capacitance		--	671	--	pF
C _{rss}	Reverse Transfer Capacitance		--	495	--	pF
Q _g	Total Gate Charge	VDS= -15V, ID= -6A, VGS= -10V	--	37.2	--	nC
Q _{gs}	Gate-Source Charge		--	9.84	--	nC
Q _{gd}	Gate-Drain Charge		--	7.52	--	nC
Switching Characteristics (Note4)						
t _{d(on)}	Turn-on Delay Time	VDD=-15V, RL=15Ω ID=-6A, RG=3Ω, VGS=-10V	--	10	--	nS
t _r	Turn-on Rise Time		--	17	--	nS
t _{d(off)}	Turn-off Delay Time		--	63	--	nS
t _f	Turn-off Fall Time		--	37	--	nS
Source- Drain Diode Characteristics @ T_J = 25°C (unless otherwise stated)						
V _{SD}	Forward on voltage (Note3)	IS=-3.5A,VGS=0V	--	--	-1.2	V

Note:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec
3. Pulse Test: pulse width ≤ 300 us, duty cycle ≤ 2%.
4. Guaranteed by design, not subject to production testing.



-30V P-Channel Enhancement Mode MOSFET
Typical Characteristics

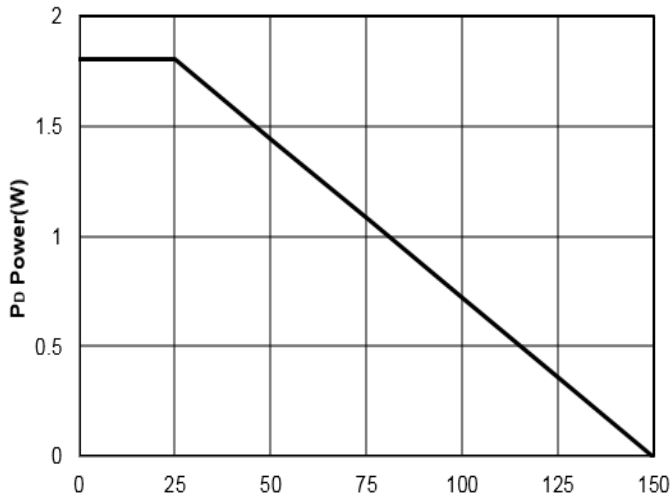


Figure1: Tj Junction Temperature (°C)

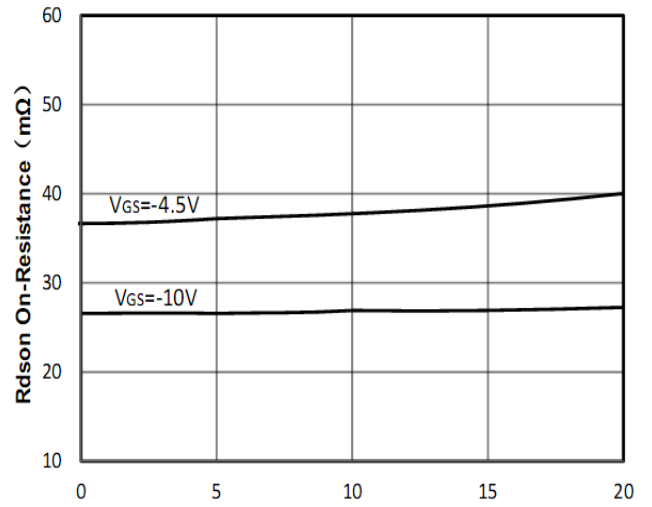


Figure2: Id Drain Current (A)

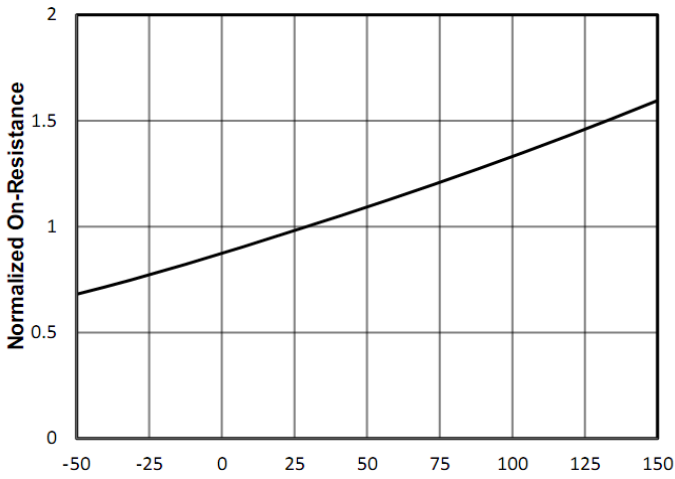


Figure3: Tj Junction Temperature (°C)

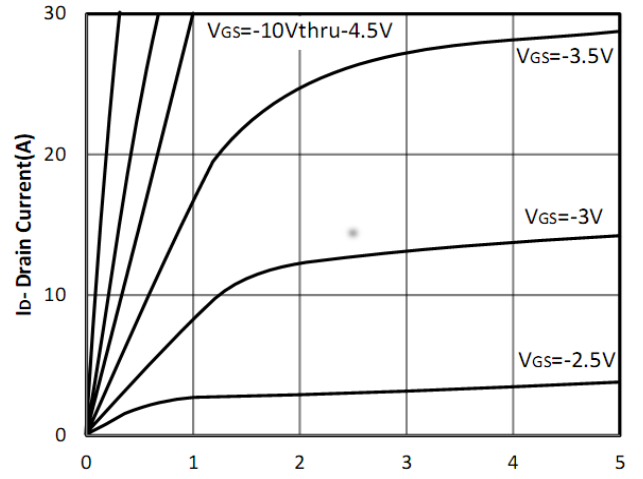


Figure4: -Vds Drain-Source Voltage (V)

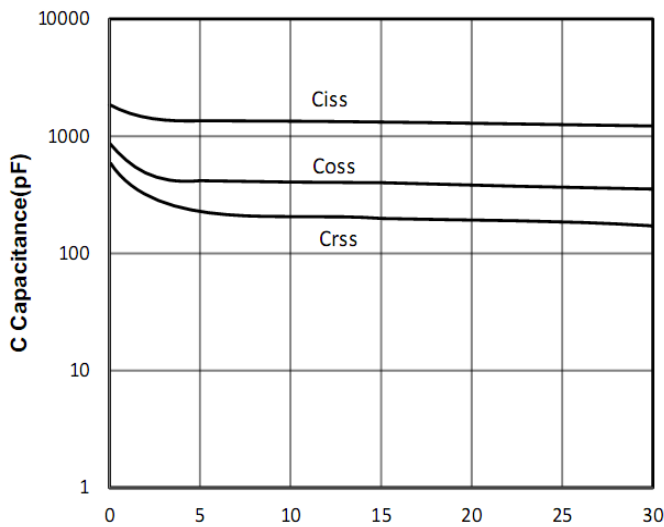


Figure5: -Vds Drain-Source Voltage (V)

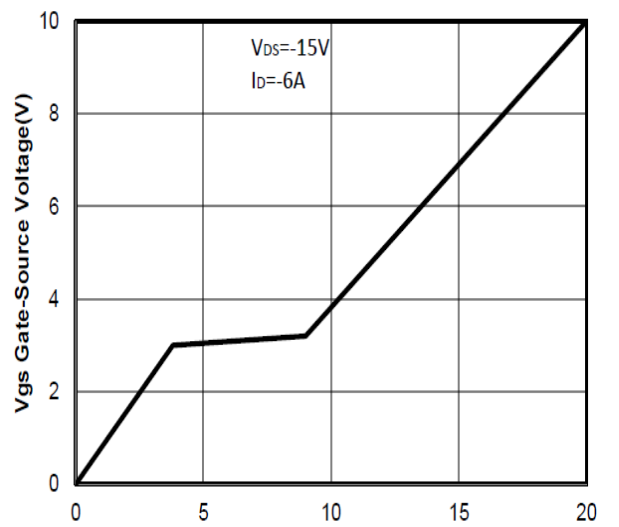


Figure6: -Qg Gate Charge (nC)



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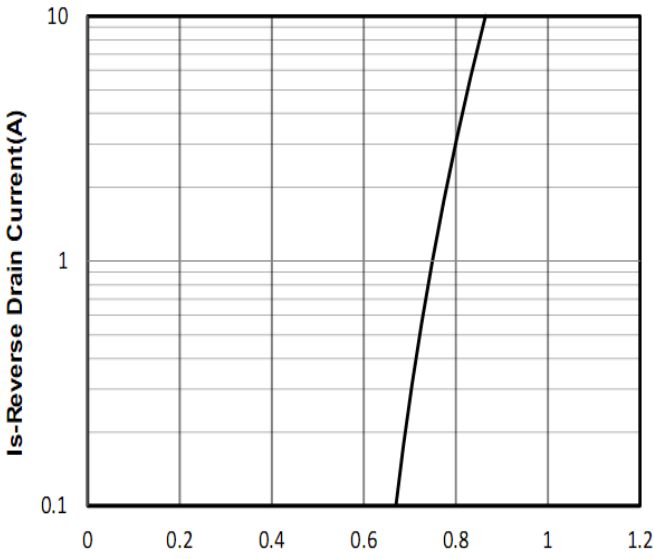


Figure7: -Vsd Source-Drain Voltage (V)

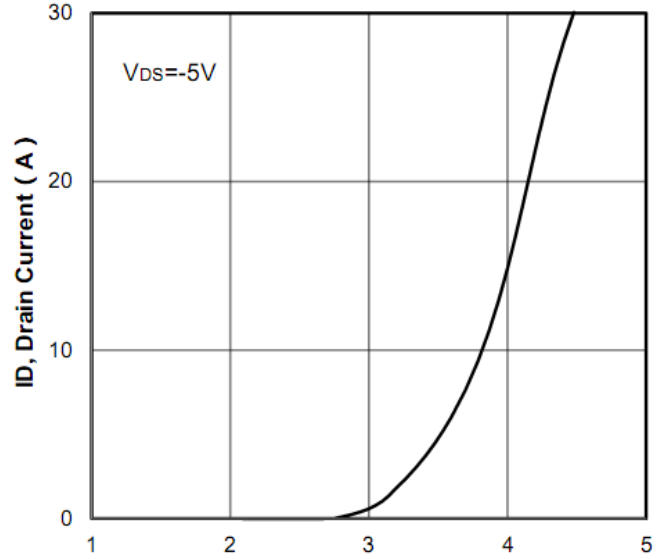


Figure8: -Vgs Gate-Source Voltage (V)

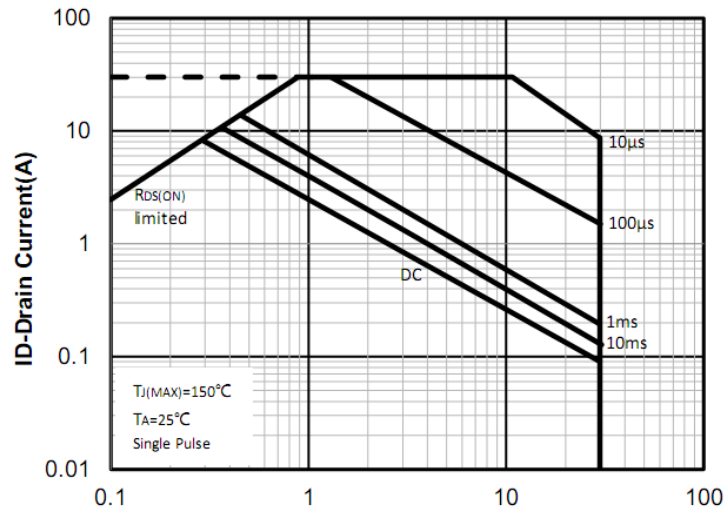


Figure9: -Vds Drain -Source Voltage (V)

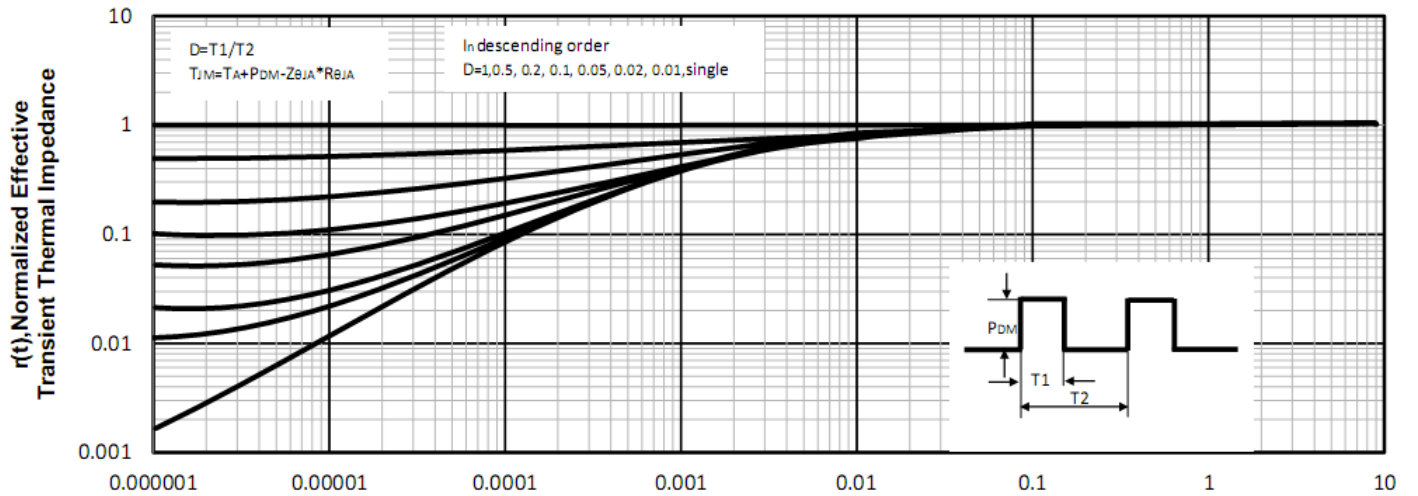


Figure10: Square Wave Pulse Duration (sec)

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Test Circuit and Waveform:

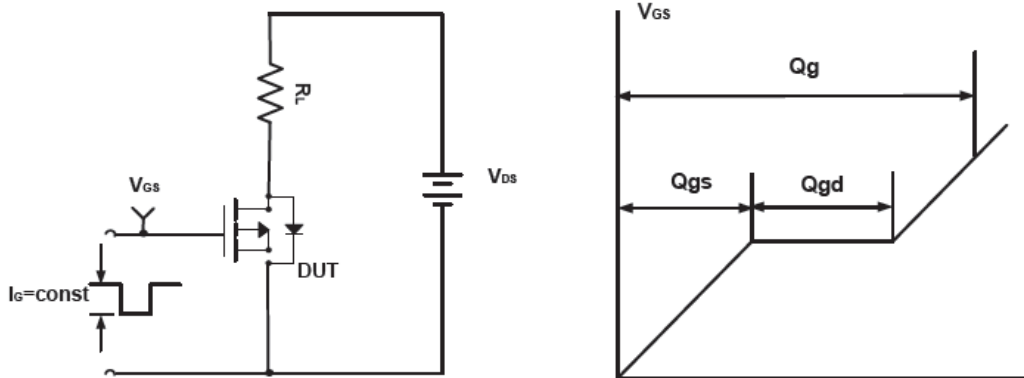


Figure A Gate Charge Test Circuit & Waveforms

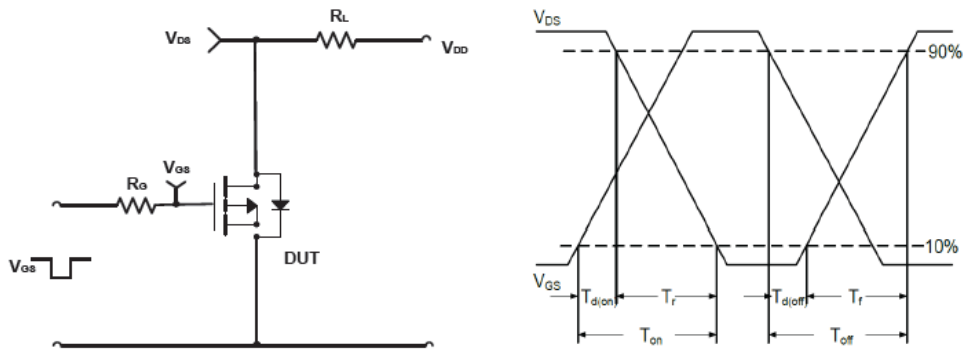


Figure B Switching Test Circuit & Waveforms

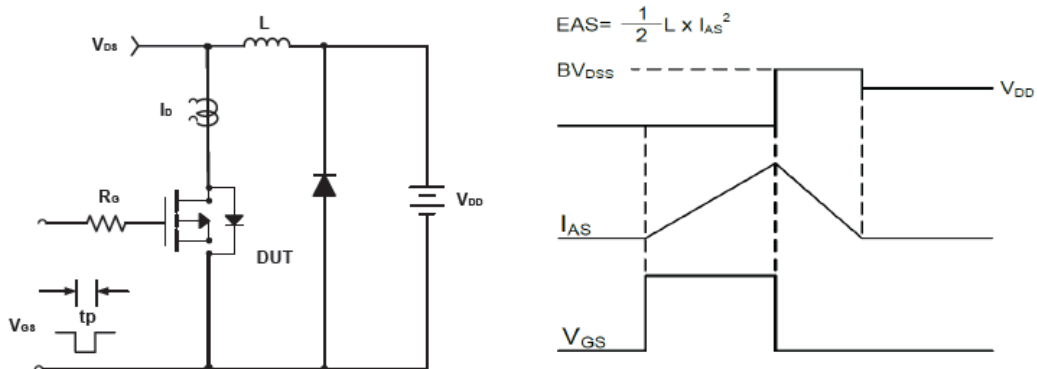
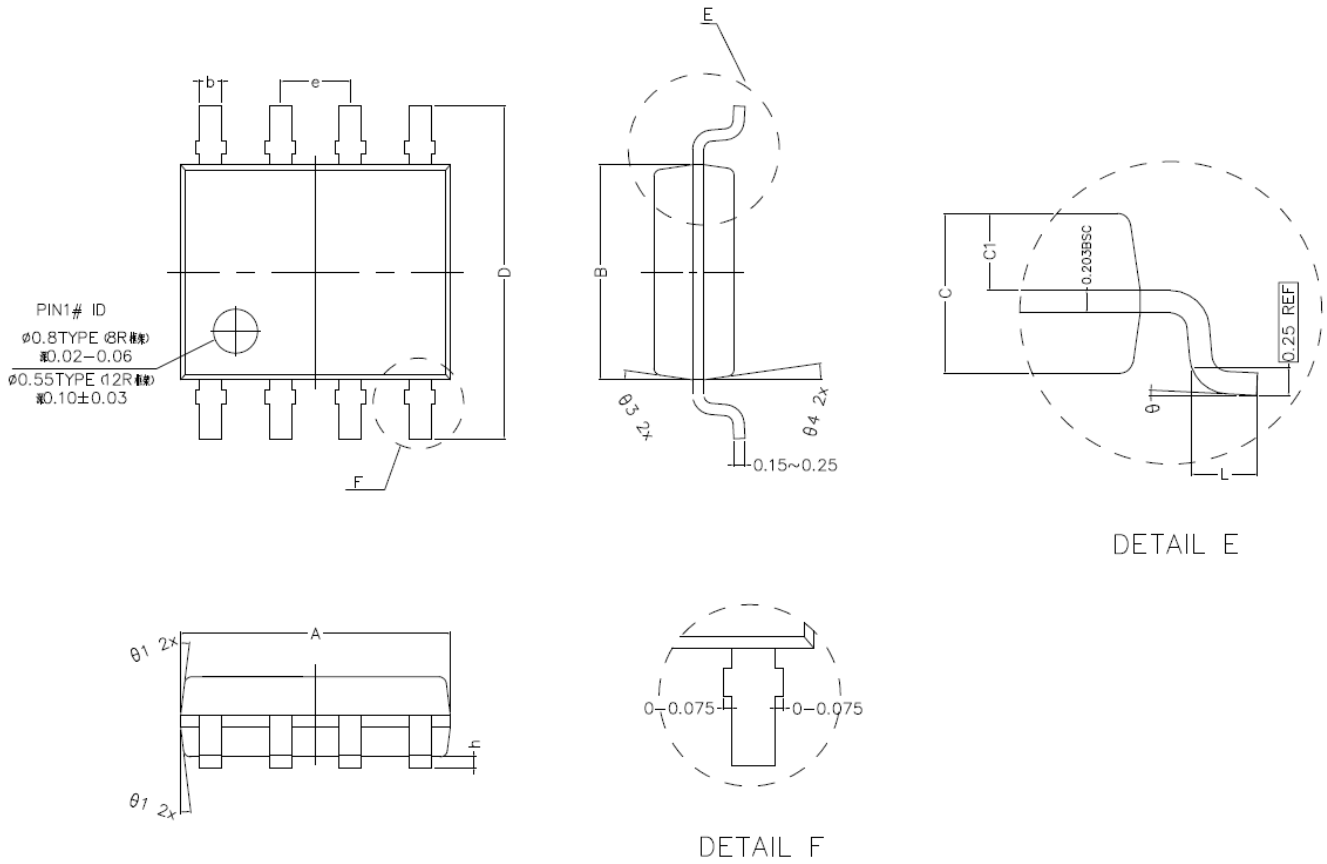


Figure C Unclamped Inductive Switching Circuit & Waveforms

-30V P-Channel Enhancement Mode MOSFET
SOP-8 Package Outline Dimensions (Units: mm)


COMMON DIMENSIONS (UNITS OF MEASURE IS mm)			
	MIN	NORMAL	MAX
A	4.800	4.900	5.000
B	3.800	3.900	4.000
C	1.350	1.450	1.550
C1	0.650	0.700	0.750
D	5.900	6.100	6.300
L	0.500	0.600	0.700
b	0.350	0.400	0.450
h	0.050	0.150	0.250
e	1.270TYPE		
θ ₁	7° TYPE(8R)		12° TYPE(12R)
θ ₂	7° TYPE(8R)		10° TYPE(12R)
θ ₃	8° TYPE(8R)		12° TYPE(12R)
θ ₄	8° TYPE(8R)		10° TYPE(12R)
θ	0° ~ 8°		